

#### **FGA10 InGaAs Photodiode**

High Speed

The FGA10 is a high-speed InGaAs photodiode with a spectral response from 700nm to 1800nm. This photodiode has a PIN structure that provides fast rise and fall times with a bias of 5V.

#### **Electrical Characteristics**

Spectral Response: 700-1800nm Active Diameter: \$\phi\_1.0mm\$

NEP@900nm:  $2.5 \times 10^{-14} \text{ W}/\sqrt{\text{Hz}}$ 

(@2V bias)

Dark Current: 100nA max (5V)

25nA (typ)

Junction Capacitance (typ): 80pF @ 0Vbias

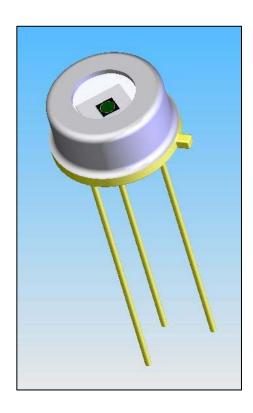
40pF @ -5V<sub>bias</sub>

Package: T05, 0.36" can

## **Maximum Ratings**

Damage Threshold CW: 100 mW/cm<sup>2</sup> Damage 10ns Pulse: 500mJ/cm<sup>2</sup>

Max Bias Voltage: 5V



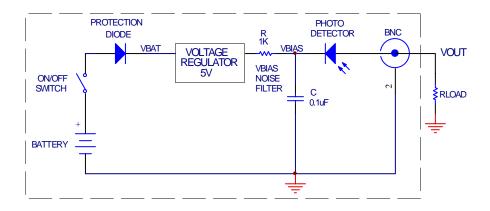
The Thorlabs FGA10 photodiode is ideal for measuring both pulsed and CW light sources, by converting the optical power to an electrical current. The InGaAs detector is housed in a T05 can, with an anode, cathode and case connection. The photodiode anode produces a current, which is a function of the incident light power and the wavelength. The responsivity  $\Re(\lambda)$ , can be read from Figure 1 to estimate the amount of photocurrent to expect. This can be converted to a voltage by placing a load resistor ( $R_{\text{LOAD}}$ ) from the photodiode anode to the circuit ground. The output voltage is derived as:

$$Vo = P * \Re(\lambda) * R_{LOAD}$$

The bandwidth,  $f_{BW}$ , and the rise time response,  $t_R$ , are determined from the diode capacitance,  $C_J$ , and the load resistance,  $R_{LOAD}$ , as shown below. Placing a bias voltage from the photo diode cathode to the circuit ground can lower the photo diode capacitance.

$$f_{BW}=1/(2\pi * R_{LOAD} * CJ),\,t_R=0.35/f_{BW}$$

# **Typical Circuit Diagram**



### **Typical Plots**

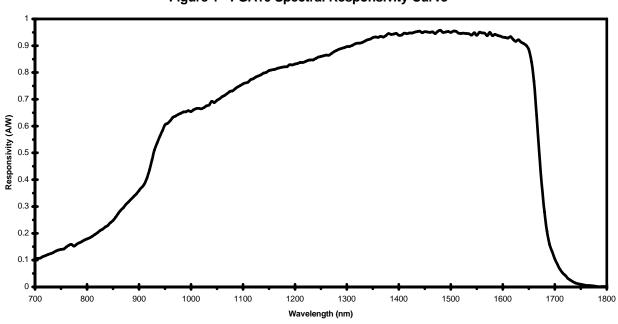


Figure 1 - FGA10 Spectral Responsivity Curve

Typical Responsivity Curve using Thorlabs calibration services.

